

Product Summary

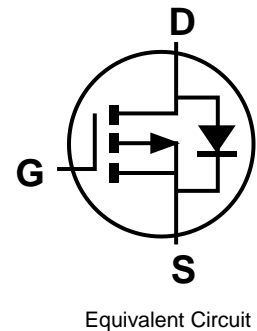
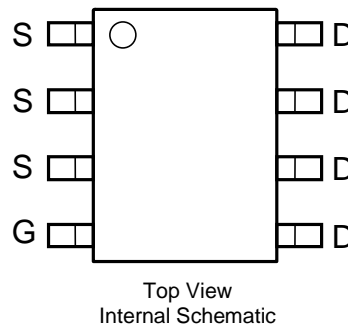
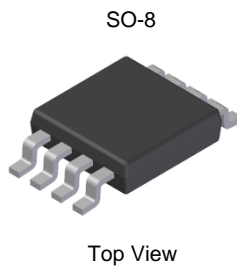
BV_{DSS}	$R_{DS(ON)}$ Max	I_D $T_A = +25^\circ C$
-40V	11m Ω @ $V_{GS} = -10V$	-11.4A
	15m Ω @ $V_{GS} = -4.5V$	-9.8A

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- DC-DC Converters
- Power Management Functions
- Analog Switch



Features and Benefits

- Rated to $+175^\circ C$ – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switch (UIS) Test in Production Low On-Resistance
- Low Input Capacitance
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **An Automotive-Compliant Part is Available Under Separate Datasheet ([DMPH4015SSSQ](#))**

Mechanical Data

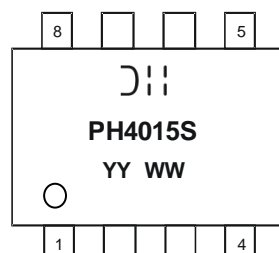
- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 ⁽³⁾
- Weight: 0.074 grams (Approximate)

Ordering Information (Note 4)

Part Number	Case	Packaging
DMPH4015SSS-13	SO-8	2,500/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



JII = Manufacturer's Marking
 PH4015S = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Year (ex: 16 = 2016)
 WW = Week (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V _{DSS}	-40	V		
Gate-Source Voltage	V _{GSS}	±25	V		
Continuous Drain Current (Note 6) V _{GS} = -10V	I _D	Steady State	T _A = +25°C	-11.4	A
			T _A = +100°C	-8.1	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	-85	A		
Maximum Body Diode Continuous Current (Note 6)	I _S	-3	A		
Avalanche Current (Note 7) L = 1mH	I _{AS}	-22	A		
Avalanche Energy (Note 7) L = 1mH	E _{AS}	260	mJ		

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	1.4	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	90	°C/W
Total Power Dissipation (Note 6)	P _D	1.8	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	70	°C/W
Thermal Resistance, Junction to Case (Note 6)	R _{θJC}	7.0	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	-40	—	—	V	V _{GS} = 0V, I _D = -250µA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1	µA	V _{DS} = -40V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±25V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	-1.5	—	-2.5	V	V _{DS} = V _{GS} , I _D = -250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	9	11	mΩ	V _{GS} = -10V, I _D = -9.8A
		—	11	15		V _{GS} = -4.5V, I _D = -9.8A
Forward Transfer Admittance	Y _{fs}	—	26	—	S	V _{DS} = -20V, I _D = -9.8A
Diode Forward Voltage	V _{SD}	—	-0.7	-1	V	V _{GS} = 0V, I _S = -1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{ISS}	—	4,234	—	pF	V _{DS} = -20V, V _{GS} = 0V f = 1MHz
Output Capacitance	C _{OSS}	—	1,036	—		
Reverse Transfer Capacitance	C _{RSS}	—	526	—		
Gate Resistance	R _G	—	7.8	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = -4.5V)	Q _g	—	42.7	—	nC	V _{DS} = -20V, I _D = -9.8A
Total Gate Charge (V _{GS} = -10V)	Q _g	—	91	—		
Gate-Source Charge	Q _{gs}	—	14.2	—		
Gate-Drain Charge	Q _{gd}	—	13.5	—		
Turn-On Delay Time	t _{D(ON)}	—	13.2	—	ns	V _{GS} = -10V, V _{DD} = -20V, R _G = 6Ω, I _D = -1A, R _L = 20Ω
Turn-On Rise Time	t _R	—	10	—		
Turn-Off Delay Time	t _{D(OFF)}	—	303	—		
Turn-Off Fall Time	t _F	—	138	—		
Reverse Recovery Time	t _{RR}	—	26	—	ns	I _F = -9.8A, di/dt = -100A/µs
Reverse Recovery Charge	Q _{RR}	—	20	—	nC	I _F = -9.8A, di/dt = -100A/µs

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 - I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

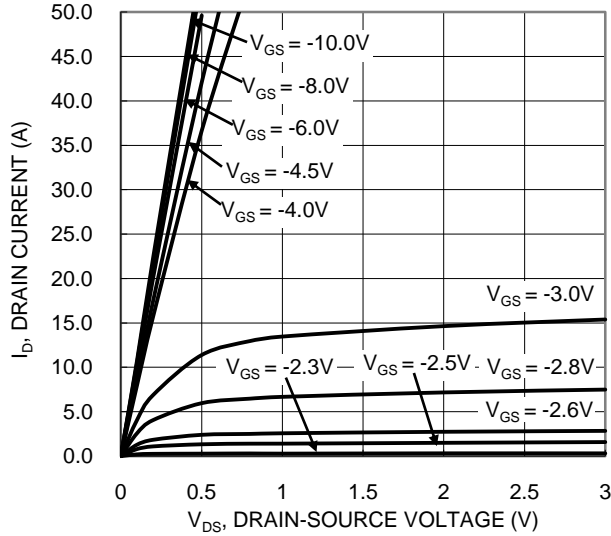


Figure 1. Typical Output Characteristic

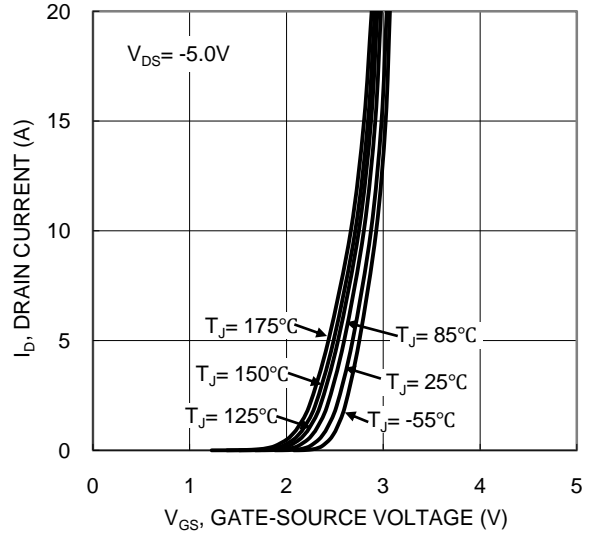


Figure 2. Typical Transfer Characteristic

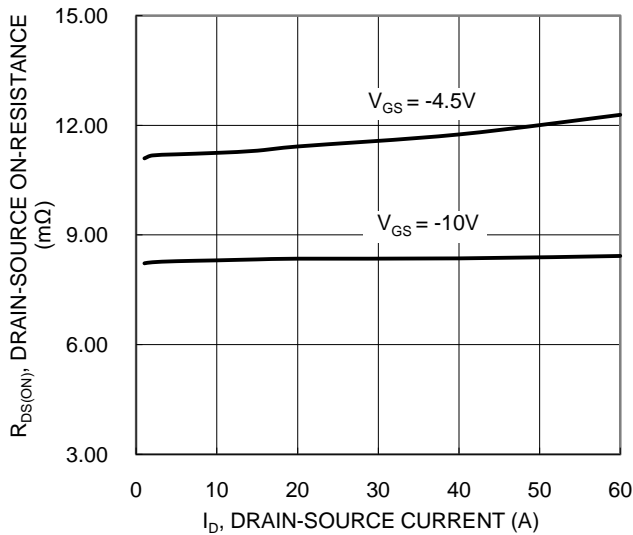


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

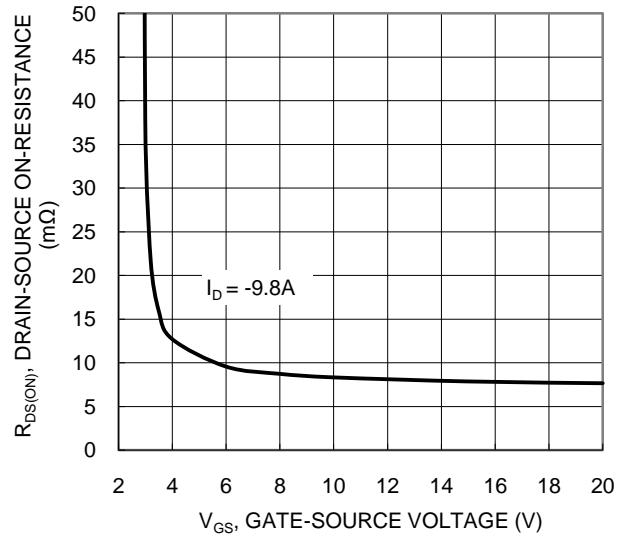


Figure 4. Typical Transfer Characteristic

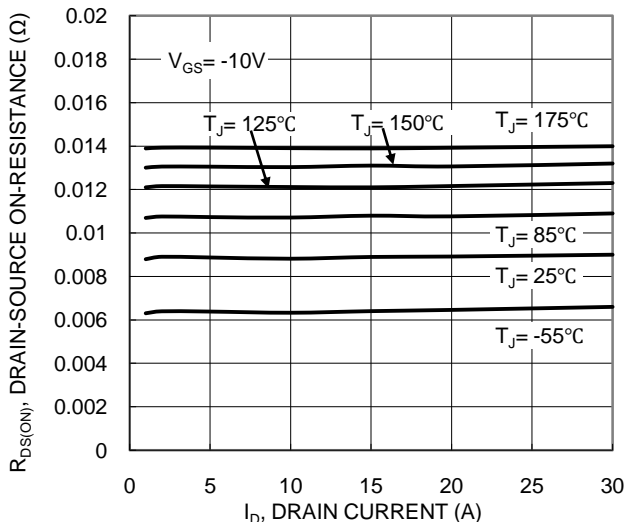


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

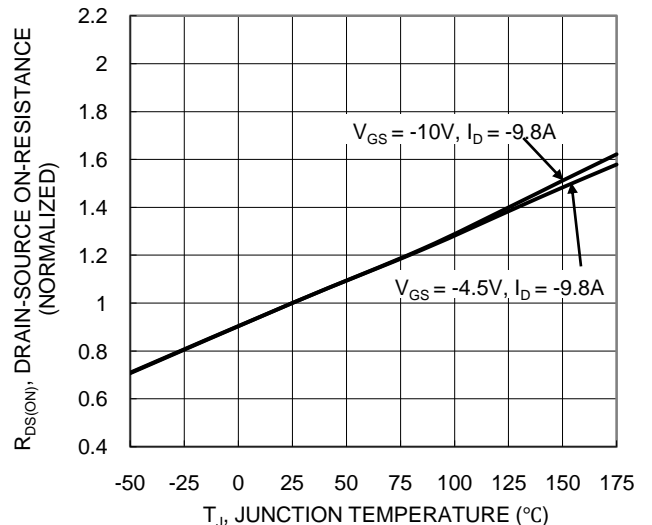
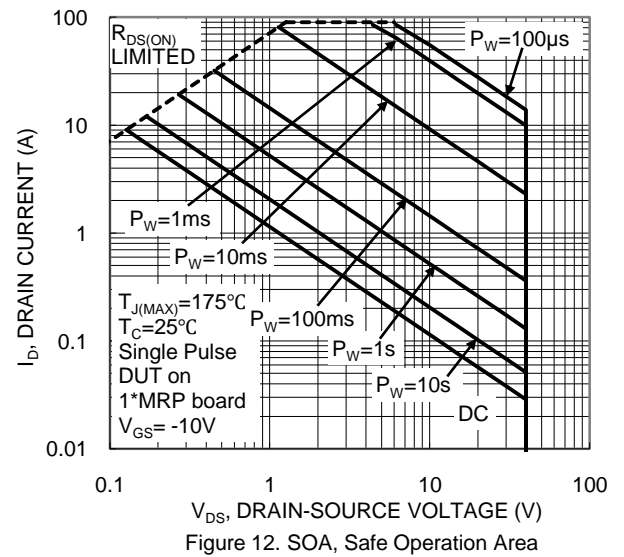
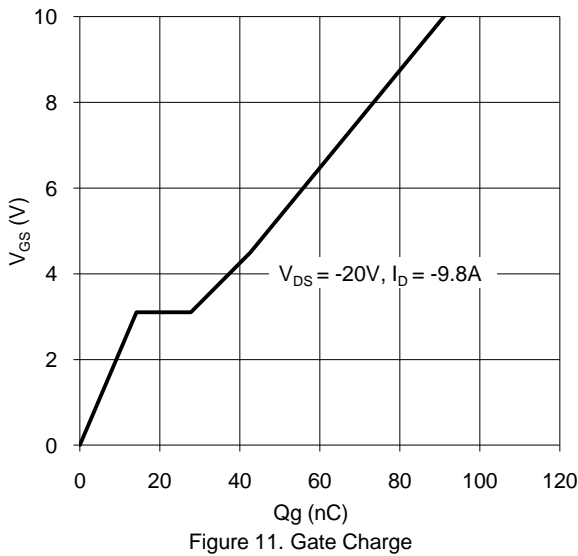
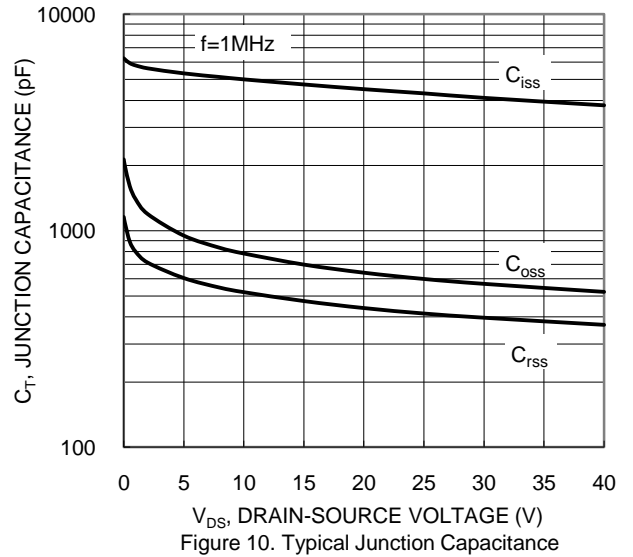
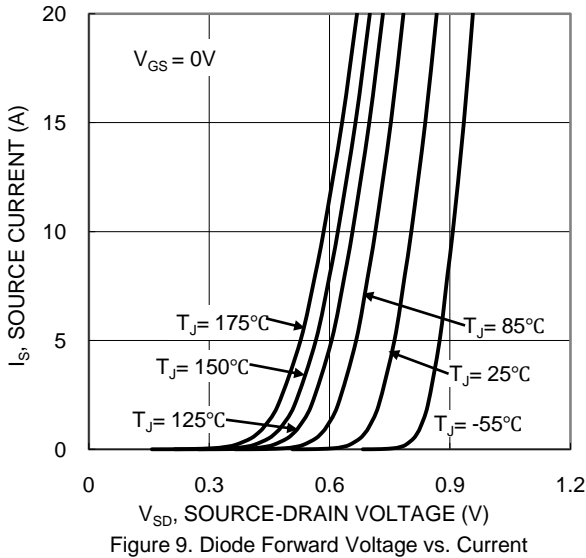
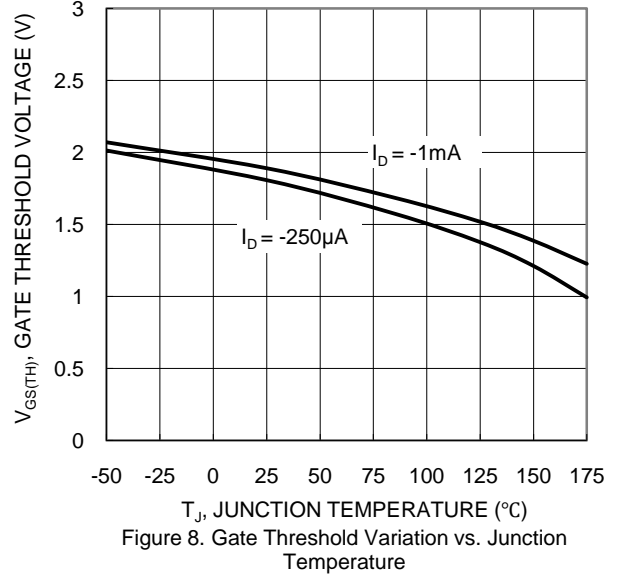
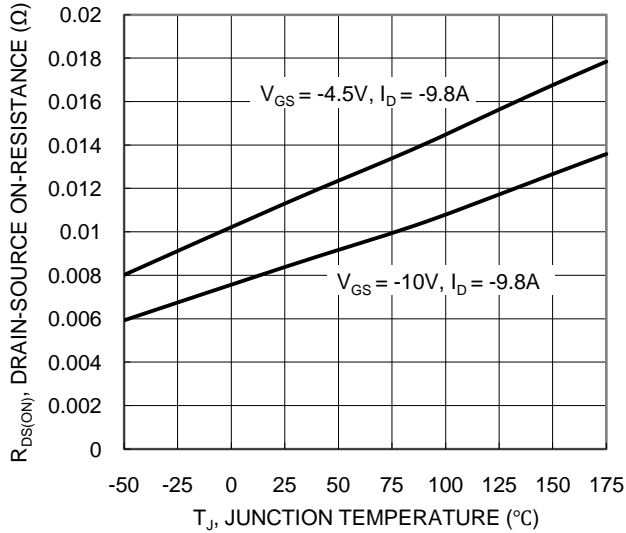


Figure 6. On-Resistance Variation with Temperature



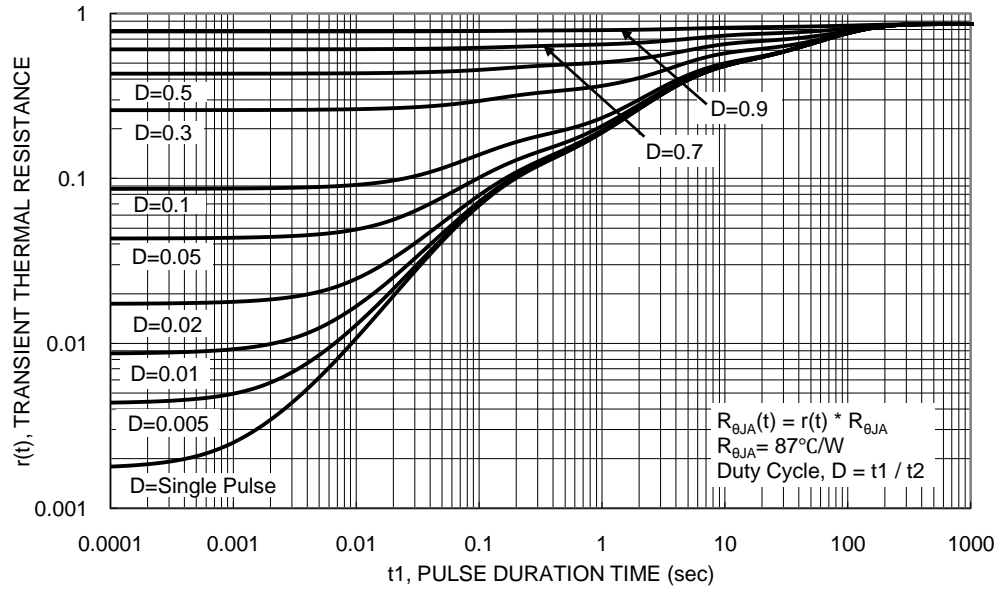
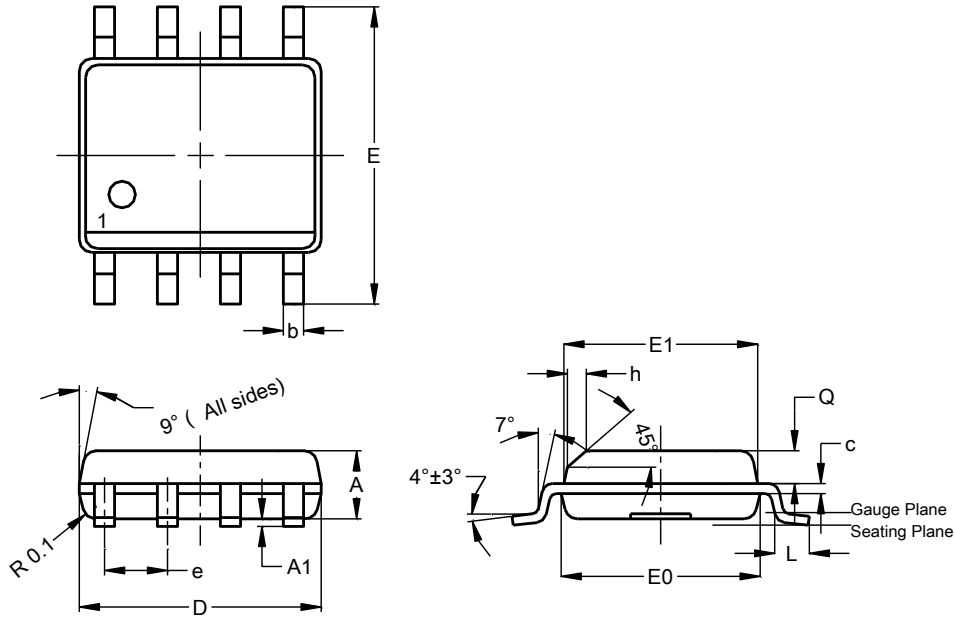


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SO-8



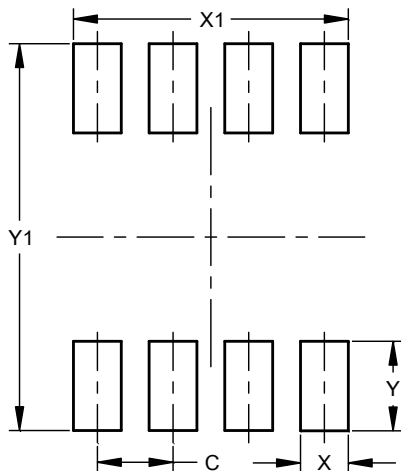
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Dim	Min	Max	Typ
A	1.40	1.50	1.45
A1	0.10	0.20	0.15
b	0.30	0.50	0.40
c	0.15	0.25	0.20
D	4.85	4.95	4.90
E	5.90	6.10	6.00
E1	3.80	3.90	3.85
E0	3.85	3.95	3.90
e	--	--	1.27
h	-	--	0.35
L	0.62	0.82	0.72
Q	0.60	0.70	0.65

All Dimensions in mm

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

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Dimensions	Value (in mm)
C	1.27
X	0.802
X1	4.612
Y	1.505
Y1	6.50

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